

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listing, of claims in the application:

Listing of Claims:

1. (Currently amended) A method of manufacturing a contact portion, the method comprising:

forming a first signal line on a substrate;

forming an insulating layer ~~covering-on~~ the first signal line and having a contact hole exposing a surface of the first signal line;

forming a contact layer only on the exposed surface of the first signal line through the contact hole by soaking the substrate in chemical conversion solution including a conductive material; and

forming a second signal line connected to the first signal line via the contact layer,

wherein the first signal line ~~is made of Al or Al alloy~~ comprises one of Al and Al alloy, and the second signal line ~~is made of ITO or IZO~~ comprises one of indium tin oxide (ITO) and indium zinc oxide (IZO).

2. (Canceled)

3. (Currently amended) The method of ~~claim 2~~claim 1, wherein the chemical conversion solution ~~include~~comprises at least one of W, Zr, Mo, and Cr.

4. (Currently amended) A method of manufacturing a thin film transistor array panel, the method comprising:

forming a gate line on a substrate;

forming a gate insulating layer;

forming a semiconductor layer;

forming an ohmic contact layer;

forming a data line and a drain electrode;

forming a passivation layer having a first contact hole exposing ~~the portion a~~portion of the drain electrode; and

forming a first contact layer only on the exposed ~~surface~~portion of the drain electrode through the first contact hole by soaking the substrate in chemical conversion solution including a conductive material.

5. (Canceled)

6. (Currently amended) The method of ~~claim 5~~claim 4, wherein the chemical conversion solution ~~include~~comprises at least one of W, Zr, Mo, and Cr.

7. (Currently amended) The method of claim 4, wherein the forming the passivation layer comprises forming a second contact hole exposing the end portion an end portion of one of the gate line or the data line and the data line is formed in the step of forming the passivation layer.

8. (Currently amended) The method of claim 7, wherein further comprising forming a second contact layer is formed on the exposed surface end portion of the one of the gate line or the data line and the data line through the second contact hole in the step of forming, wherein the forming the second contact layer is performed simultaneously with the forming the first contact layer.

9. (Currently amended) The method of claim 4, further comprising a step of forming a storage electrode line with the same layer as, wherein the forming the storage electrode line is performed simultaneously with the forming the gate line.

10. (Currently amended) The method of ~~claim 8~~ claim 9, wherein a second contact hole exposing ~~the end portion~~ an end portion of the storage electrode line is formed in the ~~step of forming the passivation layer.~~

11. (Currently amended) The method of ~~claim 9~~ claim 10, wherein further comprising forming a second contact layer is formed on the exposed surface end portion of the storage electrode line through the second contact hole in the step of

forming, wherein the forming the second contact layer is performed simultaneously with the forming the first contact layer.

12. (Currently amended) A contact portion comprising:

a substrate;

a first signal line formed on ~~a substrate~~ the substrate;

an insulating layer covering the first signal line and having a contact hole exposing a surface of the first signal line;

a contact layer disposed only on the exposed surface of the first signal line through the contact hole; and

a second signal line formed on the insulating layer and connected to the first signal line via the contact layer,

wherein the first signal line ~~is made of Al or Al alloy~~ comprises one of Al and Al alloy, and the second signal line ~~is made of ITO or IZO~~ comprises one of indium tin oxide (ITO) and indium zinc oxide (IZO).

13. (Currently amended) The contact portion of claim 12, wherein the contact layer ~~include~~ comprises at least one of W, Zr, Mo, Cr, and an alloy including at least one of W, Zr, Mo, and Cr.

14. (Original) The contact portion of claim 12, further comprising a lower layer formed under the first signal line.

15. (Original) The contact portion of claim 14, wherein the lower layer is a conductive layer including at least one of Cr, Ti, Mo, and MoW alloy.

16. (Currently amended) A thin film transistor array panel comprising:
a substrate;
a gate line formed on a substrate ~~the substrate~~;
a gate insulating layer covering the gate line;
a semiconductor layer formed on the gate insulating layer;
a data line intersecting the gate line and ~~having comprising~~ a source electrode, ~~the source electrode~~ overlapping ~~the portion of~~ the semiconductor layer;
a drain electrode overlapping ~~the portion of~~ the semiconductor layer;
a passivation layer ~~covering~~ disposed on the data line and the drain electrode, and having a first contact hole exposing ~~the portion a portion of~~ the drain electrode;
a first contact layer formed on the exposed surface of the drain electrode through the first contact hole, and ~~made of comprising~~ a conductive oxide layer; and
a pixel electrode formed on the passivation layer and connected to the drain electrode via the first contact layer.

17. (Original) The panel of claim 16, further comprising a color filter formed on the data line and the drain electrode.

18. (Original) The panel of claim 16, further comprising a storage electrode line formed with the same layer as the gate line.

19. (Original) The panel of claim 18, wherein the storage electrode line includes Al and Al alloy.

20. (Currently amended) The panel of claim 18, wherein the passivation layer and the gate insulating layer have a second contact hole exposing ~~the portion~~ a portion of the storage electrode line, and the panel further comprising comprises:
a second contact layer formed on the exposed portion on the storage electrode line through the second contact hole; and
a contact assistant connected to the exposed portion of the storage electrode line via the second contact layer.

21. (Currently amended) The panel of claim 20, wherein the second contact layer ~~include~~ comprises at least one of W, Zr, Mo, Cr, and an alloy including W, Zr, Mo, Cr.

22. (Currently amended) The panel of claim 16, wherein

~~one of the passivation layer or the and the gate insulating layer have a third~~
~~has a second contact hole exposing the portion a portion of one of the gate line or the~~
~~and the data line, and~~

~~the panel further comprising-comprises:~~

a ~~third-second~~ contact layer formed on the exposed portion on the gate line or
the data line through the ~~third-second~~ contact hole; and

a contact assistant connected to the exposed portion of the ~~one of the~~ gate line
~~or the and the~~ data line via the ~~third-second~~ contact layer.

23. (Currently amended) The panel of claim 22, wherein the ~~third-second~~
contact layer ~~include-comprises~~ at least one of W, Zr, Mo, Cr, and an alloy including
W, Zr, Mo, Cr.

24. (Currently amended) The panel of claim 16, further comprising an
ohmic contact layer formed between the data line ~~and the semiconductor layer and~~
~~between~~ the drain electrode, ~~and the and the~~ semiconductor layer.

25. (Currently amended) The panel of claim 24, wherein the ohmic contact
layer has the same planar shape as the data line and the drain electrode, and the
semiconductor layer has the ~~same~~ planar shape as the data line and the drain electrode
except for the ~~channel-a channel~~ portion between the drain electrode and the source
electrode.

26. (Currently amended) The panel of claim 16, wherein the first contact layer ~~include comprises~~ at least one of W, Zr, Mo, Cr, and an alloy including W, Zr, Mo, Cr.

27. (Original) The panel of claim 16, wherein the gate line includes a conductive layer made of Al or Al alloy.

28. (Original) The panel of claim 16, wherein the data line includes a first conductive layer made of Al or Al alloy.

29. (Currently amended) The panel of claim 28, wherein the data line further comprises a second conductive layer formed under the first conductive layer.

30. (Original) The panel of claim 29, wherein the second conductive layer is made of a conductive layer including at least one of Cr, Ti, Mo, and MoW alloy.